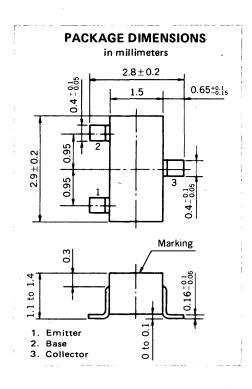


### SILICON TRANSISTOR

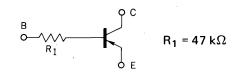
## FN1L4Z

# MEDIUM SPEED SWITCHING RESISTOR BUILT-IN TYPE PNP TRANSISTOR MINI MOLD



#### **FEATURES**

• Resistor Built-in TYPE



Complementary to FA1L4Z

#### **ABSOLUTE MAXIMUM RATINGS**

Maximum Voltages and Currents ( $T_a = 25$	°C)		
Collector to Base Voltage	$V_{CBO}$	-60	V
Collector to Emitter Voltage	V <sub>CEO</sub>	-50	. V
Emitter to Base Voltage	$V_{EBO}$	-5	V
Collector Current (DC)	Ic	-100	mΑ
Collector Current (Pulse)	Ic	-200	mΑ
Maximum Power Dissipation			
Total Power Dissipation			
at 25 °C Ambient Temperature	$P_T$	200	mW
. Maximum Temperatures			
Junction Temperature	$T_{j}$	150	°C
Storage Temperature Range	$T_{stq}$	-55 to +150	°C

#### ELECTRICAL CHARACTERISTICS (T<sub>a</sub> = 25 °C)

CHARACTERISTIC	SYMBOL	MIN.	TYP.	MAX.	UNIT	TEST CONDITIONS	
Collector Cutoff Current	ІСВО			-100	nA	V <sub>CB</sub> = -50 V, I <sub>E</sub> = 0	
DC Current Gain	hFE1*	135	230	600		V <sub>CE</sub> = -5.0 V, I <sub>C</sub> = -5.0 mA	
DC Current Gain	hFE2*	100	190			V <sub>CE</sub> = -5.0 V, I <sub>C</sub> = -50 mA	
Collector Saturation Voltage	V <sub>CE(sat)</sub> *		-0.07	-0.2	V	$I_C = -5.0 \text{ mA}, I_B = -0.25 \text{ mA}$	
Low-Level Input Voltage	VIL*		-0.58	-0.5	V	$V_{CE} = -5.0 \text{ V, } I_{C} = -100 \mu \text{A}$	
High-Level Input Voltage	V <sub>IH</sub> *	-4.0	-1.8		V	V <sub>CE</sub> = -0.2 V, I <sub>C</sub> = -5.0 mA	
Input Resistor	R <sub>1</sub>	32.9	47.0	61.1	kΩ		
Turn-on Time	t <sub>on</sub>			0.2	μs	$V_{CC}$ = -5 V, $V_{in}$ = -5 V $R_L$ = 1 kΩ $PW$ = 2 $\mu$ s, Duty Cycle $\leq$ 2 %	
Storage Time	t <sub>stg</sub>			5.0	μs		
Turn-off Time	toff			6.0	μs		

<sup>\*</sup> Pulsed: PW  $\leq$  350  $\mu$ s, Duty Cycle  $\leq$  2 %

#### h<sub>FE</sub> Classification

· <del>-</del>				
Marking	M61	M62	M63	
hFE1	135 to 270	200 to 400	300 to 600	

#### TYPICAL CHARACTERISTICS (Ta = 25 °C)

